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प्लाज़्मा अनुसंधान संस्थान
INSTITUTE FOR PLASMA RESEARCH
परमाणु ऊर्जा विभाग, भारत सरकार का एक सहायता प्राप्त संस्थान
An Aided Institute of Department of Atomic Energy,
Government of India



इन्दिरा पुल के पास, भट, गांधीनगर - 382 428 भारत
दूरभाष: (079) 2396 2020/2021/2028
फैक्स: 91-079-23962277
वेब: www.ipr.res.in

NEAR INDIRA BRIDGE, BHAT
DIST. GANDHINAGAR - 382 428 (INDIA)
Phone: (079) 2396 2000/2026/2332
Fax : 91-079-23962277
Web : www.ipr.res.in

ENQUIRY

ENQUIRY NO : IPR/EQF/18-19/098
Date : 01-08-2018

Due on : 06-09-2018 by 1:00 PM IST

Please send your offer in sealed envelope specifying Enquiry No, Date & Due Date, ALONG WITH your credentials for the following items which we are interested to import directly against Foreign Trade Policy 2015-2020.

Important Note:

Please note that e-mail quotations are not acceptable however you may send your queries (if any) to importpurchase@ipr.res.in

Please ensure your sealed quotation reaches this office not later than above mentioned due date and time.

Kindly go through the following documents properly before quoting which are available on the IPR web portal i.e., http://www.ipr.res.in/documents/tender_terms.html / attached herewith.

- 1) Instructions to the bidders & Terms and conditions (refer Form No: **IPR-FP-01.V3**)
- 2) Bidding format

GST for Goods and Services (IGST/CGST/SGST TAX BENEFITS): Please refer **clause no: 14** of Form No: **IPR-FP-01.V3**

QUOTATION SHOULD BE ADDRESSED TO PURCHASE OFFICER ONLY

Sr No	Description	Quantity
1	GaSb wafers, Diameter: 76.2 mm, Thickness: 625 +/- 25 micron, semiconducting, un-doped	3.0 Nos.

Note: Please quote with complete technical details (Technical compliance sheet and product data sheet).

Encl: Refer attached sheet for detailed technical specification.

Sd/-

Mr. D. Ramesh
Purchase Officer-II

Information to Vendors: We are working towards a single platform for our future requirement. Hence, please refer IPR website i.e., <http://www.ipr.res.in/documents/tendersenq.html> for our future requirement.

1PB/G&F/18-19/098 (1/2)

Technical specifications of GaSb wafer

- 1) Orientation: <100>
- 2) Conductivity: Semi-conducting
- 3) Diameter: 76.2 mm (3'')
- 4) Thickness: 625 +/- 35 um
- 5) Surface: one side polished
- 6) Grade: Epi Polished grade
- 7) Dopant: Undopped

Compliance form

Sl. No	Particulars	IPR Requirement	Vendor's specification
1.	Orientation	<100>	
2.	Diameter	76.2mm	
3.	Thickness	625±35µm	
4.	Conductivity	Semiconducting	
5	Surface	One side polished	
6	Grade	Epi polished grade	
7	Dopant	Un-doped	